

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for CDMA, W-CDMA and LTE base station applications with frequencies from 1930 to 1990 MHz. Can be used in Class AB and Class C for all typical cellular base station modulation formats.

- Typical Single-Carrier W-CDMA Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 1100$ mA, $P_{out} = 34$ Watts Avg., IQ Magnitude Clipping, Channel Bandwidth = 3.84 MHz, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF.

Frequency	G_{ps} (dB)	η_D (%)	Output PAR (dB)	ACPR (dBc)
1930 MHz	18.8	31.7	6.4	-38.5
1960 MHz	19.1	31.4	6.5	-38.8
1990 MHz	19.3	31.5	6.5	-38.8

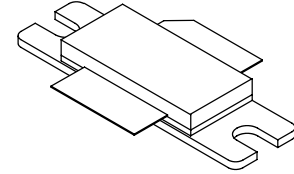
- Capable of Handling 10:1 VSWR, @ 32 Vdc, 1960 MHz, 191 Watts CW Output Power (3 dB Input Overdrive from Rated P_{out})
- Typical P_{out} @ 1 dB Compression Point \approx 138 Watts CW

Features

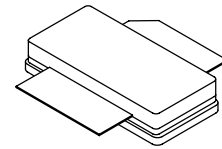
- 100% PAR Tested for Guaranteed Output Power Capability
- Characterized with Series Equivalent Large-Signal Impedance Parameters and Common Source S-Parameters
- Internally Matched for Ease of Use
- Integrated ESD Protection
- Greater Negative Gate-Source Voltage Range for Improved Class C Operation
- Designed for Digital Predistortion Error Correction Systems
- Optimized for Doherty Applications
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MRF8S19140HR3
MRF8S19140HSR3

1930-1990 MHz, 34 W AVG., 28 V
CDMA, W-CDMA, LTE
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465-06, STYLE 1
NI-780
MRF8S19140HR3



CASE 465A-06, STYLE 1
NI-780S
MRF8S19140HSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-6.0, +10	Vdc
Operating Voltage	V_{DD}	32, +0	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature (1,2)	T_J	225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case Case Temperature 75°C, 34 W CW, 28 Vdc, $I_{DQ} = 1100$ mA, 1960 MHz Case Temperature 80°C, 140 W CW, 28 Vdc, $I_{DQ} = 1100$ mA, 1960 MHz	$R_{\theta JC}$	0.48 0.45	°C/W

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 200\ \mu\text{Adc}$)	$V_{GS(th)}$	1.0	1.8	2.5	Vdc
Gate Quiescent Voltage ($V_{DD} = 28\text{ Vdc}$, $I_D = 1100\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	1.9	2.6	3.4	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 3\text{ Adc}$)	$V_{DS(on)}$	0.1	0.24	0.3	Vdc

Functional Tests ⁽¹⁾ (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 1100\text{ mA}$, $P_{out} = 34\text{ W Avg.}$, $f = 1960\text{ MHz}$, Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset.

Power Gain	G_{ps}	18.0	19.1	21.0	dB
Drain Efficiency	η_D	30.0	31.4	—	%
Output Peak-to-Average Ratio @ 0.01% Probability on CCDF	PAR	5.9	6.5	—	dB
Adjacent Channel Power Ratio	ACPR	—	-38.8	-37.5	dBc
Input Return Loss	IRL	—	-24	-7	dB

Typical Broadband Performance (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 1100\text{ mA}$, $P_{out} = 34\text{ W Avg.}$, Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset.

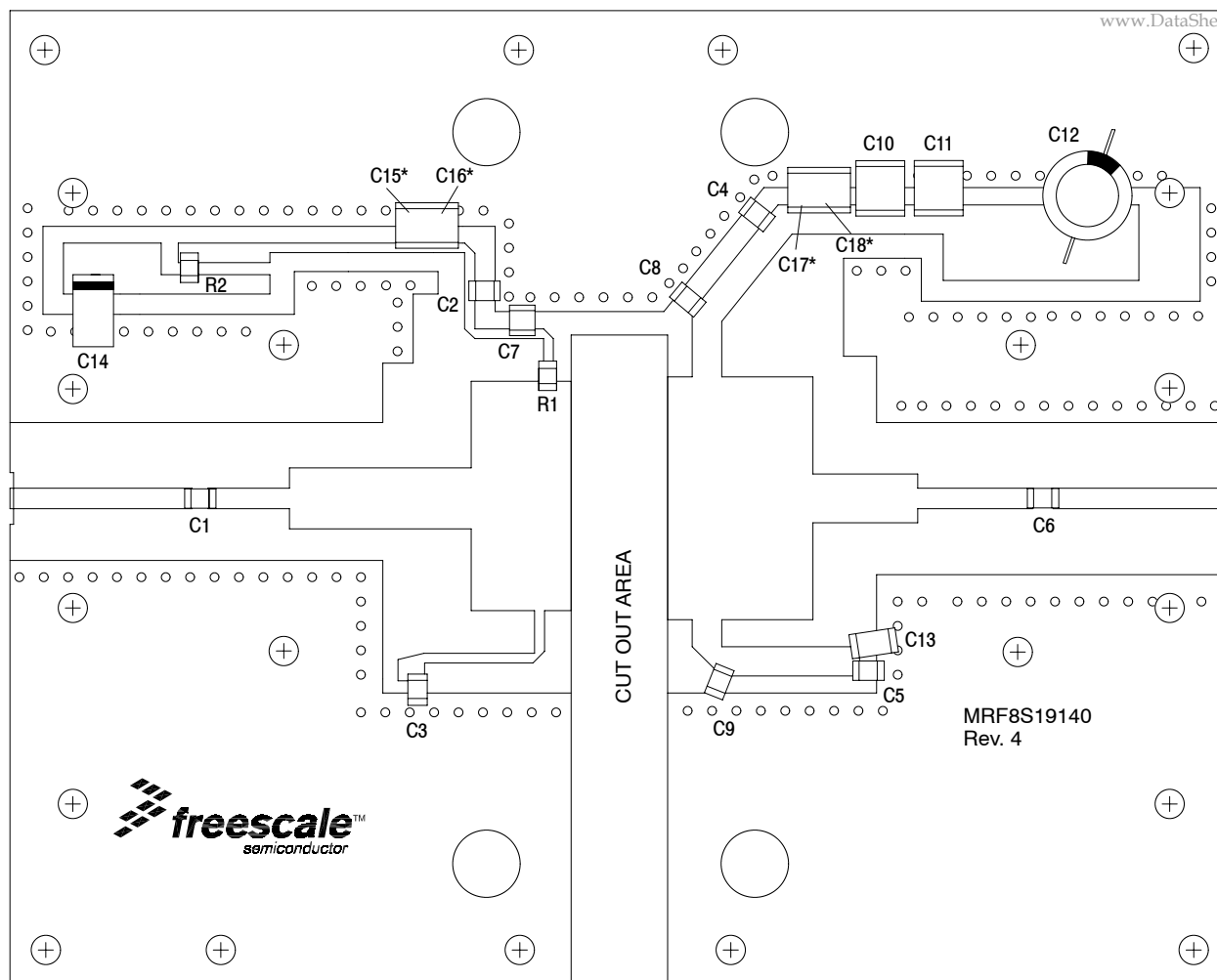
Frequency	G_{ps} (dB)	η_D (%)	Output PAR (dB)	ACPR (dBc)	IRL (dB)
1930 MHz	18.8	31.7	6.4	-38.5	-24
1960 MHz	19.1	31.4	6.5	-38.8	-24
1990 MHz	19.3	31.5	6.5	-38.8	-15

1. Part internally matched both on input and output.

(continued)

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
Typical Performances (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 1100\text{ mA}$, 1930–1990 MHz Bandwidth					
P_{out} @ 1 dB Compression Point, CW	P1dB	—	138	—	W
IMD Symmetry @ 55 W PEP, P_{out} where IMD Third Order Intermodulation $\cong 30\text{ dBc}$ (Delta IMD Third Order Intermodulation between Upper and Lower Sidebands > 2 dB)	IMD _{sym}	—	15	—	MHz
VBW Resonance Point (IMD Third Order Intermodulation Inflection Point)	VBW _{res}	—	68	—	MHz
Gain Flatness in 60 MHz Bandwidth @ $P_{out} = 34\text{ W Avg.}$	G _F	—	0.5	—	dB
Gain Variation over Temperature (-30°C to $+85^\circ\text{C}$)	ΔG	—	0.017	—	dB/ $^\circ\text{C}$
Output Power Variation over Temperature (-30°C to $+85^\circ\text{C}$)	ΔP_{1dB}	—	0.010	—	dBm/ $^\circ\text{C}$



*Stacked

Figure 1. MRF8S19140HR3(HSR3) Test Circuit Component Layout

Table 5. MRF8S19140HR3(HSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1, C2, C3, C4, C5, C6	10 pF Chip Capacitors	ATC100B110JT500XT	ATC
C7, C8, C9	0.8 pF Chip Capacitors	ATC800B0R8BT500XT	ATC
C10, C11	10 μ F, 50 V Chip Capacitors	GRM55DR61H106KA88L	Murata
C12	330 μ F, 63 V Electrolytic Capacitor	MCRH63V337M13X21-RH	Multicomp
C13	6.8 μ F, 50 V Chip Capacitor	C4532X7R1H685KT	TDK
C14	47 μ F, 16 V Tantalum Capacitor	T491D476K016AT	Kemet
C15, C17	.01 μ F, 100 V Chip Capacitors	C1825C103K1GACTU	Kemet
C16, C18	.56 μ F, 50 V Chip Capacitors	C1825C564J5RACTU	Kemet
R1	5.1 Ω , 1/8 W Chip Resistor	CRCW08055R10JNEA	Vishay
R2	4.75 Ω , 1/4 W Chip Resistor	CRCW12064R75FNEA	Vishay
PCB	0.030", $\epsilon_r = 2.55$	AD255A	Arlon

TYPICAL CHARACTERISTICS

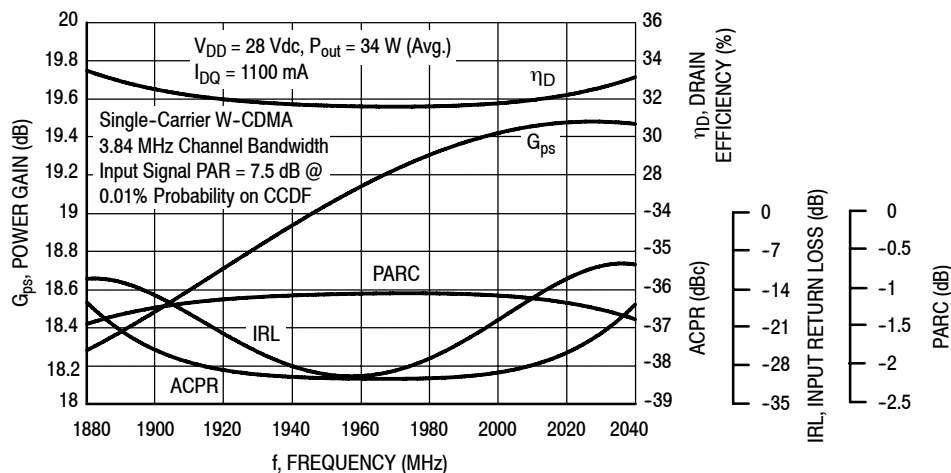


Figure 2. Output Peak-to-Average Ratio Compression (PARC) Broadband Performance @ $P_{out} = 34$ Watts Avg.

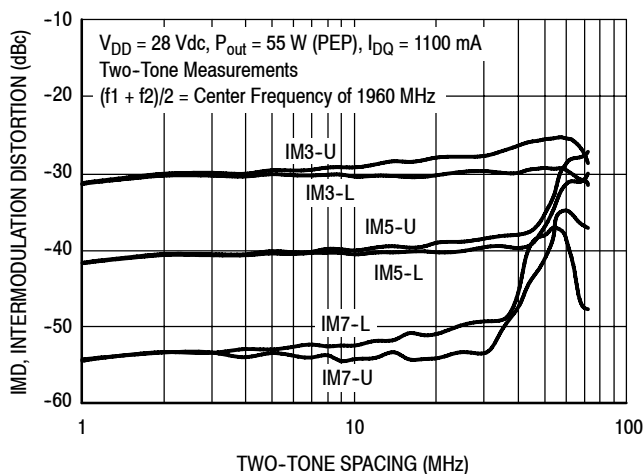


Figure 3. Intermodulation Distortion Products versus Two-Tone Spacing

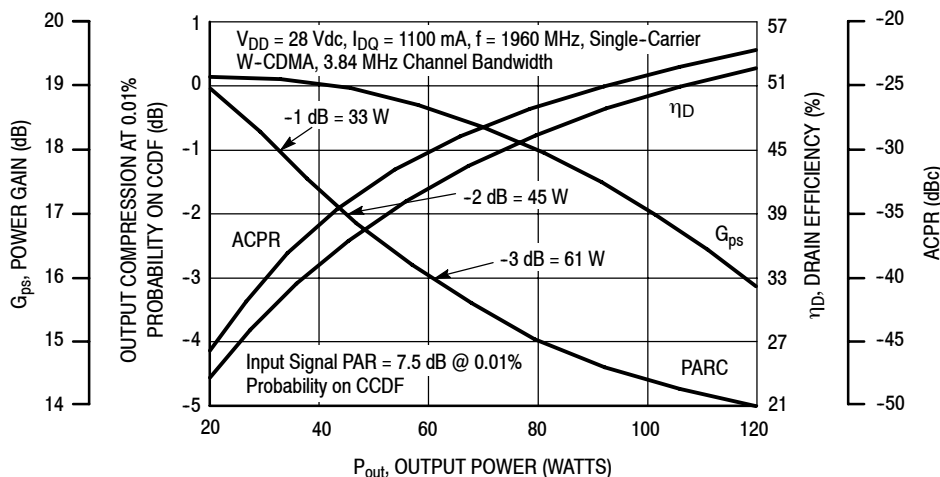


Figure 4. Output Peak-to-Average Ratio Compression (PARC) versus Output Power

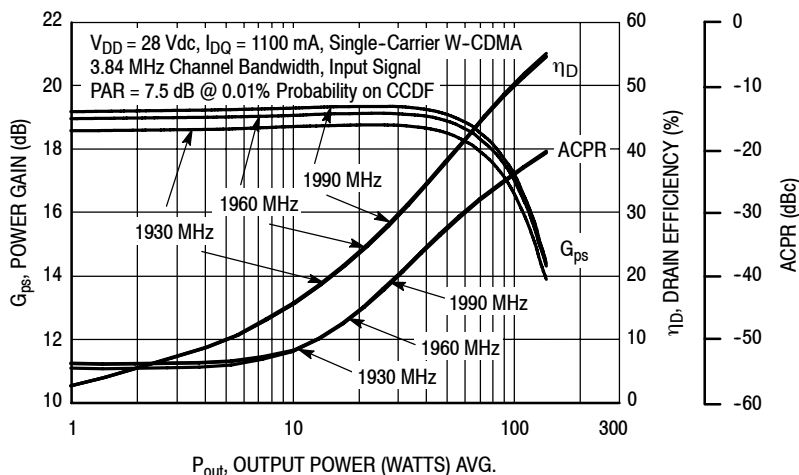


Figure 5. Single-Carrier W-CDMA Power Gain, Drain Efficiency and ACPR versus Output Power

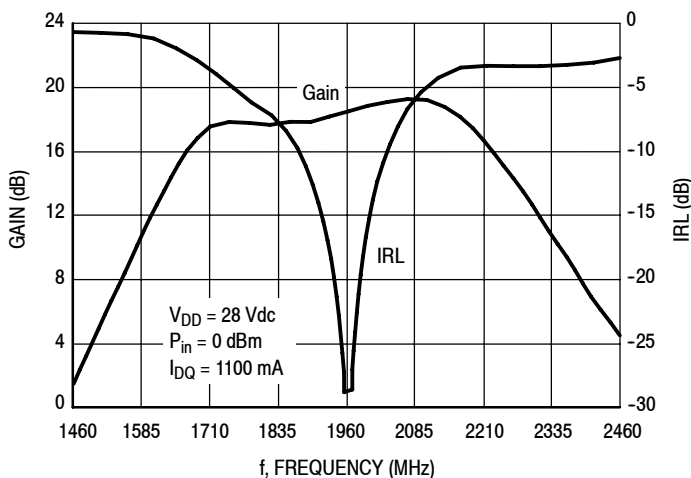


Figure 6. Broadband Frequency Response

W-CDMA TEST SIGNAL

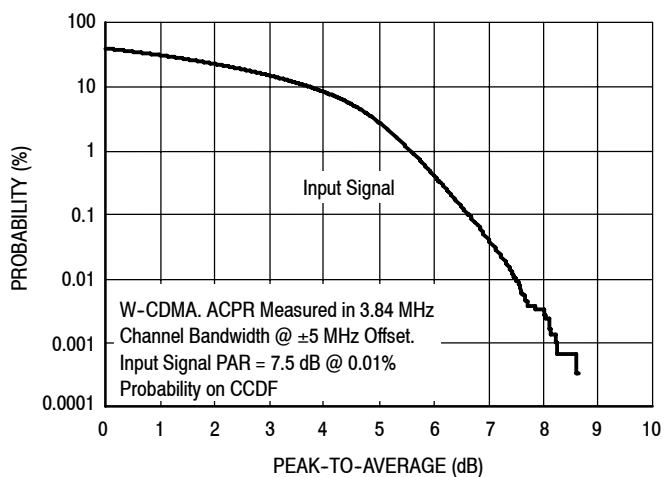


Figure 7. CCDF W-CDMA IQ Magnitude Clipping, Single-Carrier Test Signal

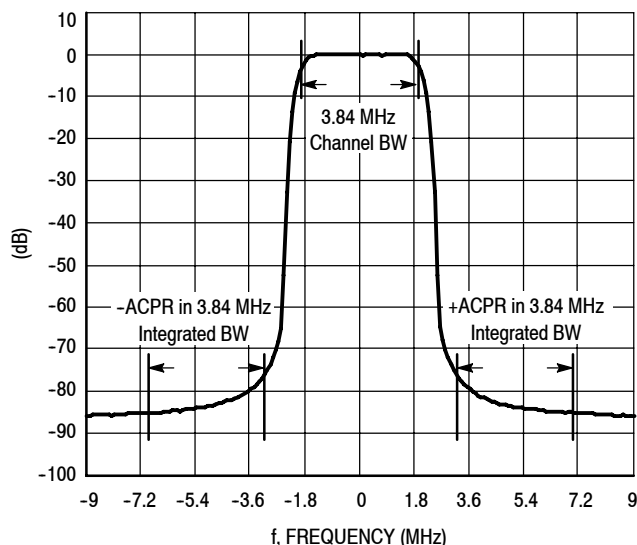


Figure 8. Single-Carrier W-CDMA Spectrum

$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 1100 \text{ mA}$, $P_{out} = 34 \text{ W Avg.}$

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f MHz	Z_{source} Ω	Z_{load} Ω
1880	4.27 - j3.42	1.62 - j3.54
1900	4.33 - j3.32	1.61 - j3.45
1920	4.40 - j3.22	1.61 - j3.36
1940	4.47 - j3.12	1.60 - j3.27
1960	4.54 - j3.02	1.60 - j3.18
1980	4.61 - j2.93	1.60 - j3.09
2000	4.69 - j2.84	1.59 - j3.00
2020	4.73 - j2.80	1.59 - j2.96
2040	4.63 - j2.80	1.59 - j2.96

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

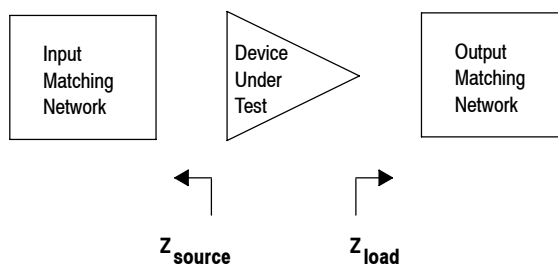
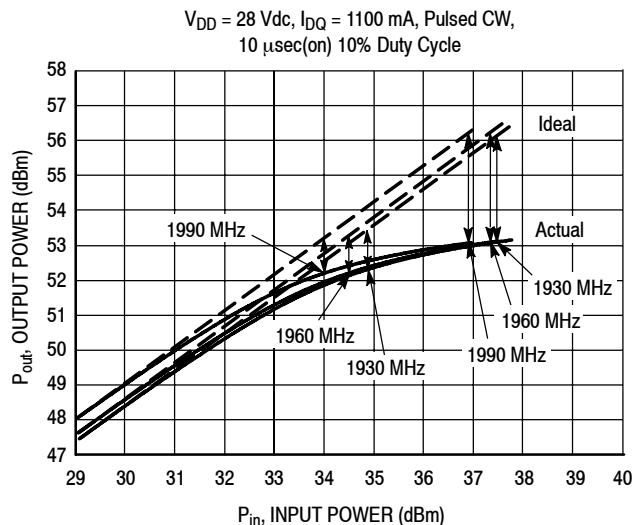


Figure 9. Series Equivalent Source and Load Impedance



NOTE: Load Pull Test Fixture Tuned for Peak P1dB Output Power @ 28 V

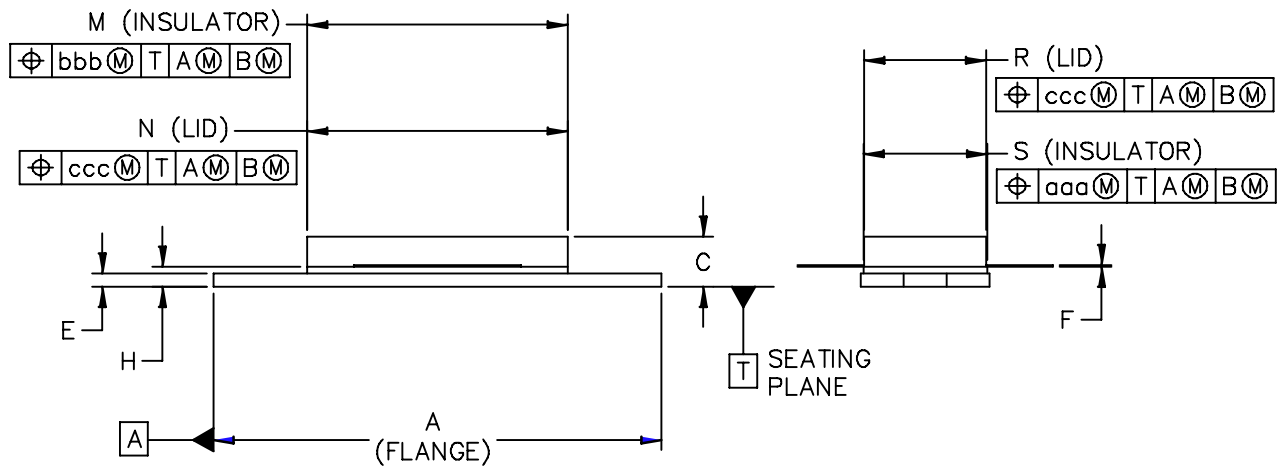
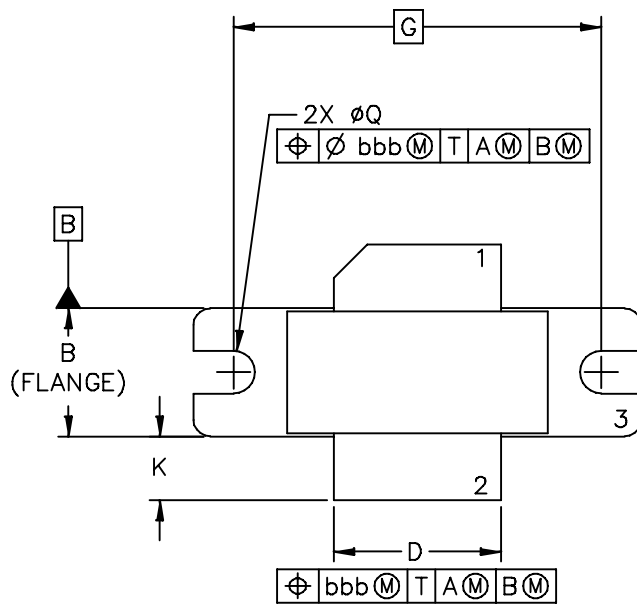
f (MHz)	P1dB		P3dB	
	Watts	dBm	Watts	dBm
1930	170	52.3	207	53.1
1960	165	52.2	205	53.1
1990	166	52.2	203	53.1

Test Impedances per Compression Level

f (MHz)		Z_{source} Ω	Z_{load} Ω
1930	P1dB	4.97 - j5.89	1.28 - j2.16
1960	P1dB	7.33 - j5.00	1.18 - j2.04
1990	P1dB	8.82 - j5.01	1.04 - j2.68

Figure 10. Pulsed CW Output Power versus Input Power @ 28 V

PACKAGE DIMENSIONS



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	<p>CASE NUMBER: 465-06</p>		<p>31 MAR 2005</p>
	<p>STANDARD: NON-JEDEC</p>		

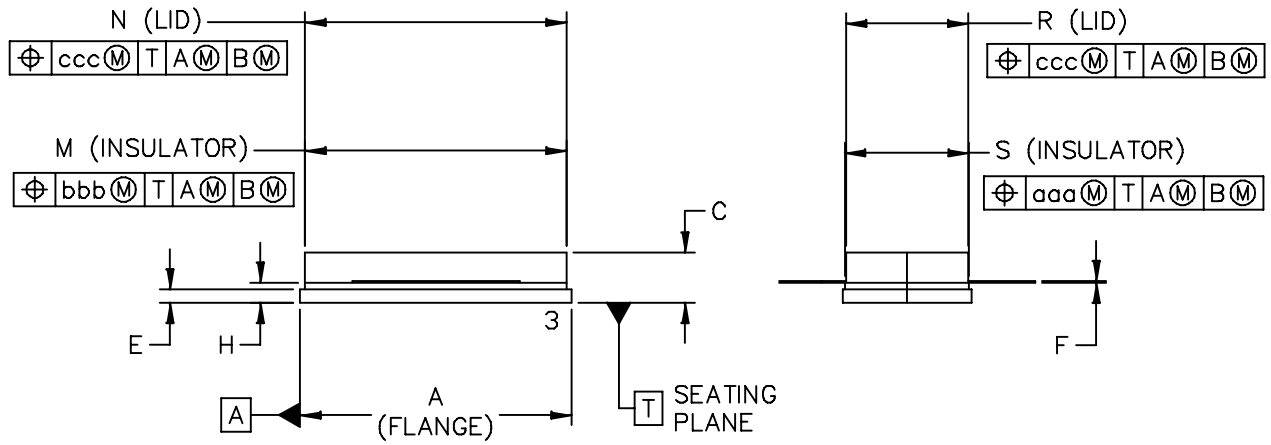
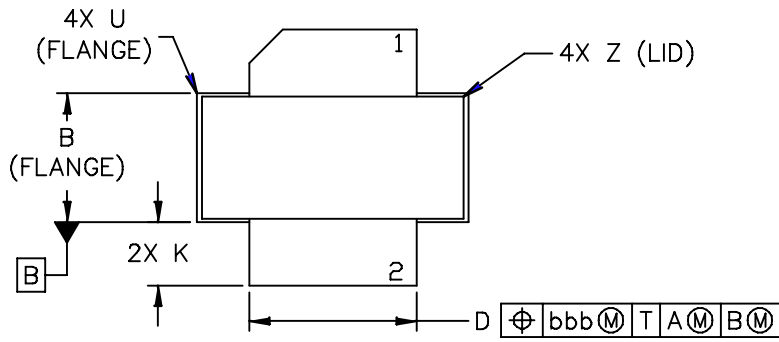
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2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED .030 (.762) AWAY FROM PACKAGE BODY.

STYLE 1:

- PIN 1. DRAIN
 2. GATE
 3. SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.335	– 1.345	33.91	– 34.16	R	.365	– .375	9.27	– 9.53
B	.380	– .390	9.65	– 9.91	S	.365	– .375	9.27	– 9.52
C	.125	– .170	3.18	– 4.32	aaa	– .005	–	– 0.127	–
D	.495	– .505	12.57	– 12.83	bbb	– .010	–	– 0.254	–
E	.035	– .045	0.89	– 1.14	ccc	– .015	–	– 0.381	–
F	.003	– .006	0.08	– 0.15	–	–	–	–	–
G	1.100 BSC		27.94 BSC		–	–	–	–	–
H	.057	– .067	1.45	– 1.7	–	–	–	–	–
K	.170	– .210	4.32	– 5.33	–	–	–	–	–
M	.774	– .786	19.66	– 19.96	–	–	–	–	–
N	.772	– .788	19.6	– 20	–	–	–	–	–
Q	∅.118	– ∅.138	∅3	– ∅3.51	–	–	–	–	–
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4. DIMENSION H IS MEASURED .030 (0.762) AWAY FROM PACKAGE BODY.

STYLE 1:

- PIN 1. DRAIN
2. GATE
3. SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	.805	– .815	20.45	– 20.7	U	–	– .040	–	– 1.02
B	.380	– .390	9.65	– 9.91	Z	–	– .030	–	– 0.76
C	.125	– .170	3.18	– 4.32	aaa	–	.005 –	–	0.127 –
D	.495	– .505	12.57	– 12.83	bbb	–	.010 –	–	0.254 –
E	.035	– .045	0.89	– 1.14	ccc	–	.015 –	–	0.381 –
F	.003	– .006	0.08	– 0.15	–	–	– –	–	– –
H	.057	– .067	1.45	– 1.7	–	–	– –	–	– –
K	.170	– .210	4.32	– 5.33	–	–	– –	–	– –
M	.774	– .786	19.61	– 20.02	–	–	– –	–	– –
N	.772	– .788	19.61	– 20.02	–	–	– –	–	– –
R	.365	– .375	9.27	– 9.53	–	–	– –	–	– –
S	.365	– .375	9.27	– 9.52	–	–	– –	–	– –

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Refer to the following documents, tools and software to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- Electromigration MTTF Calculator
- RF High Power Model
- .s2p File

For Software, do a Part Number search at <http://www.freescale.com>, and select the “Part Number” link. Go to the Software & Tools tab on the part’s Product Summary page to download the respective tool.

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	May 2010	• Initial Release of Data Sheet

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